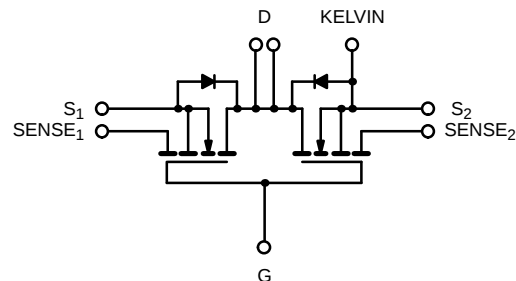
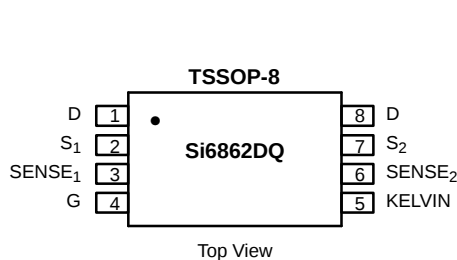




Dual N-Channel 20-V (D-S) MOSFET with Current Sense

PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
20	0.026 @ $V_{GS} = 4.5$ V	6.6
	0.036 @ $V_{GS} = 2.5$ V	5.6

TrenchFET®
Power MOSFETsABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V _{DS}	20		V
Gate-Source Voltage		V _{GS}	± 12		
Continuous Drain Current (T _J = 150°C) ^a	T _A = 25°C	I _D	6.6	5.2	A
	T _A = 70°C		5.2	4.2	
Pulsed Drain Current (10 μs Pulse Width)		I _{DM}	30		
Continuous Source Current (Diode Conduction) ^a		I _S	1.5	0.9	
Maximum Power Dissipation ^a	T _A = 25°C	P _D	1.8	1.1	W
	T _A = 70°C		1.1	0.7	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 10$ sec	R_{thJA}	55	70	$^\circ\text{C/W}$
	Steady State		93	110	
Maximum Junction-to-Foot	Steady State	R_{thJF}	36	45	

Notes

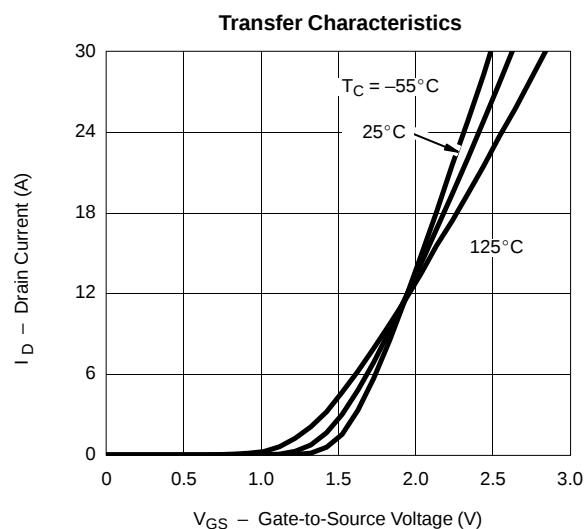
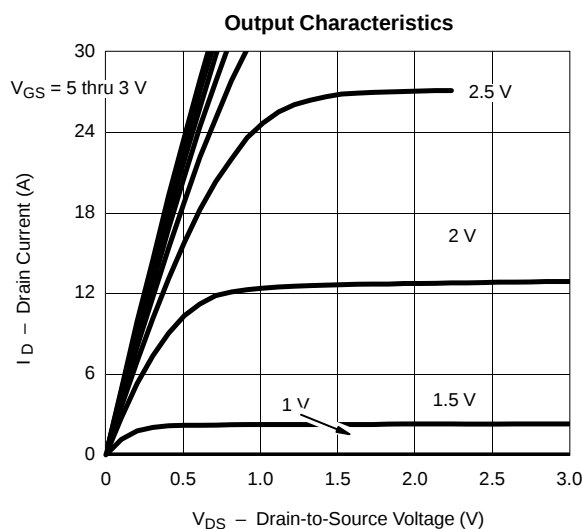
a. Surface Mounted on 1" x 1" FR4 Board.

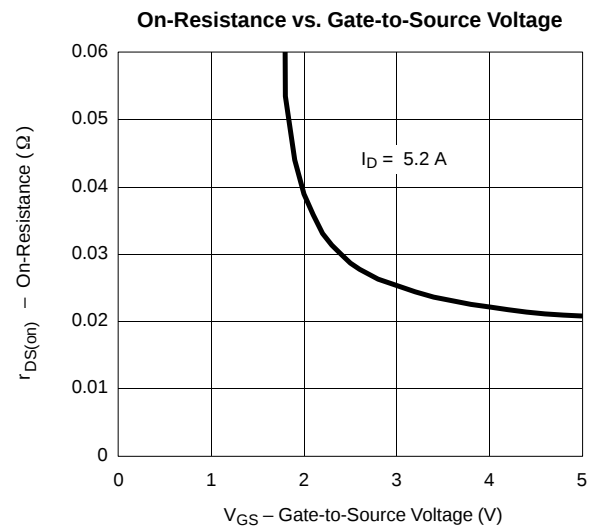
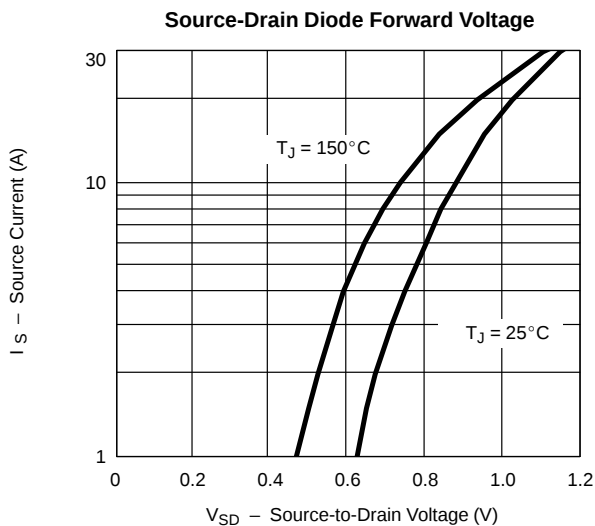
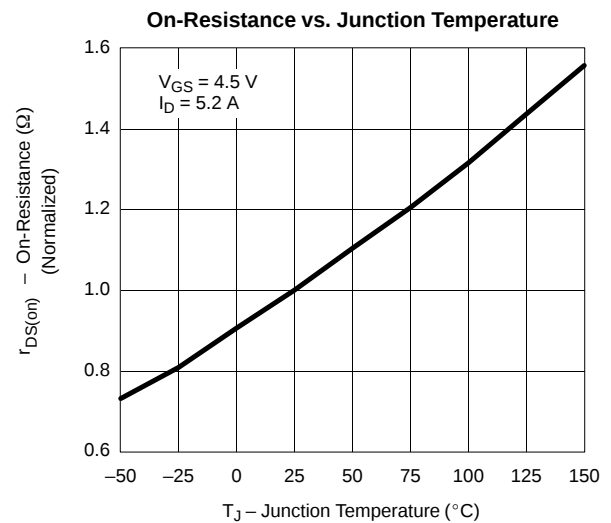
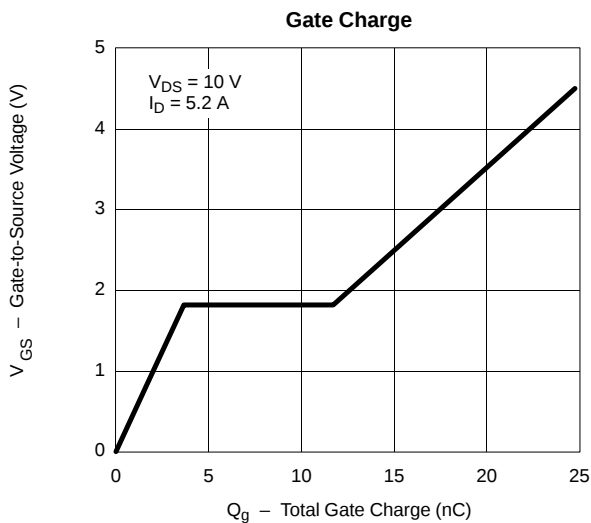
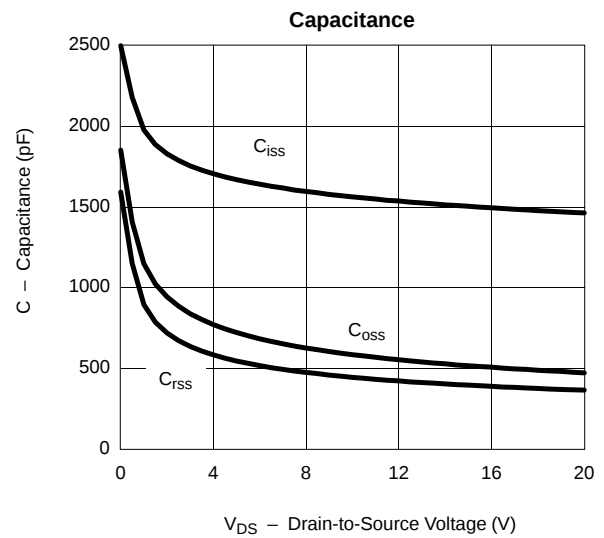
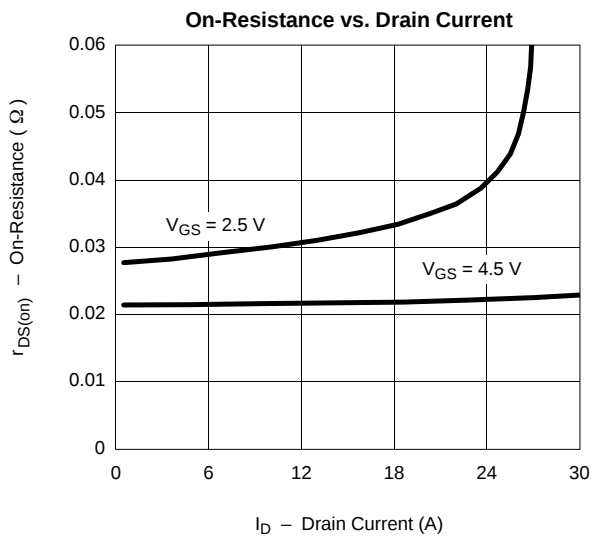
SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

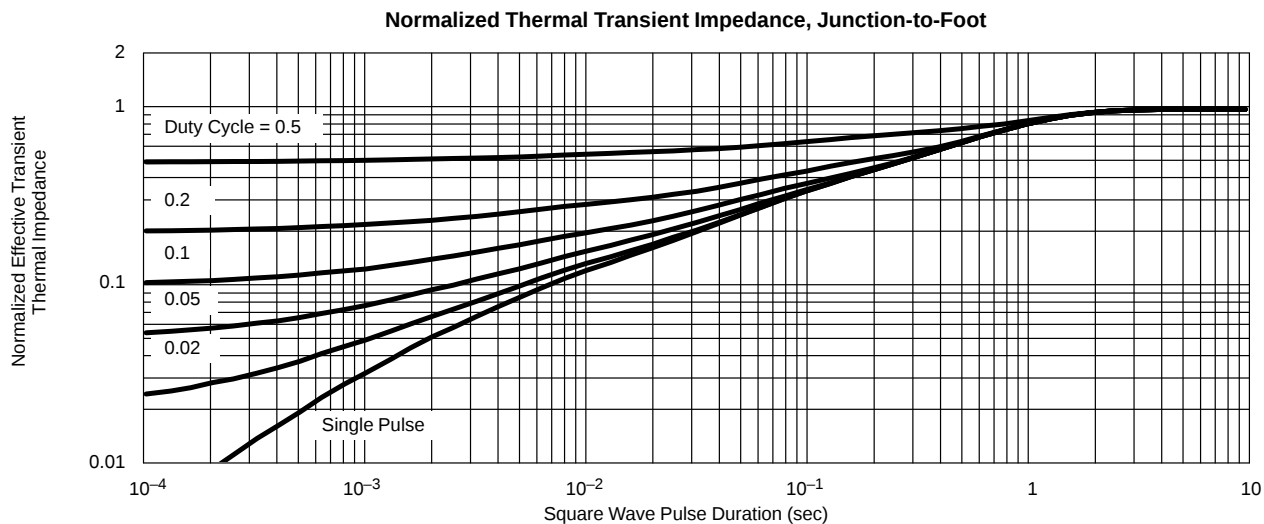
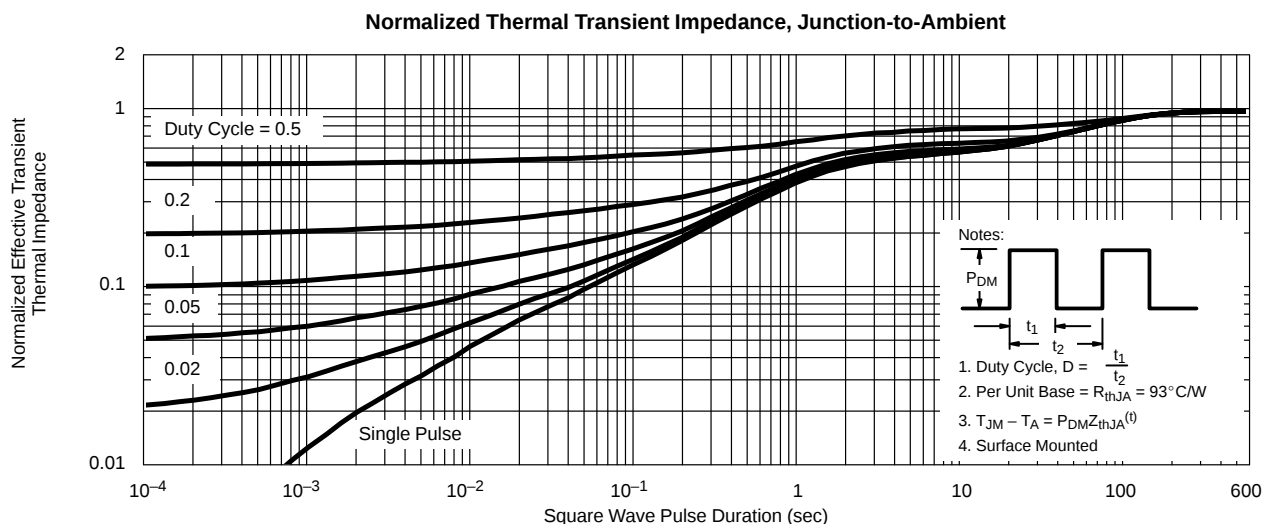
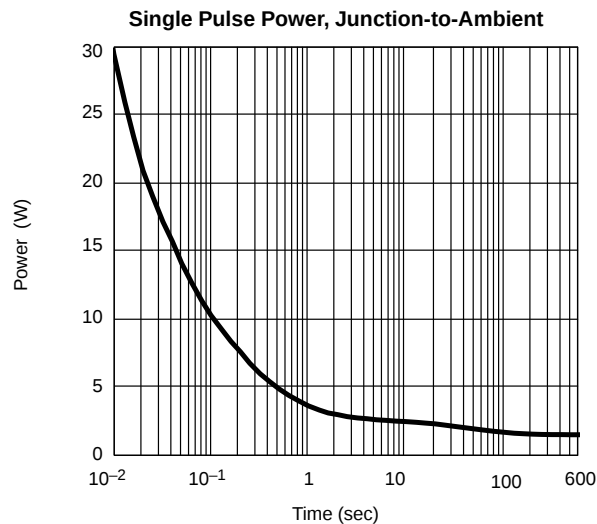
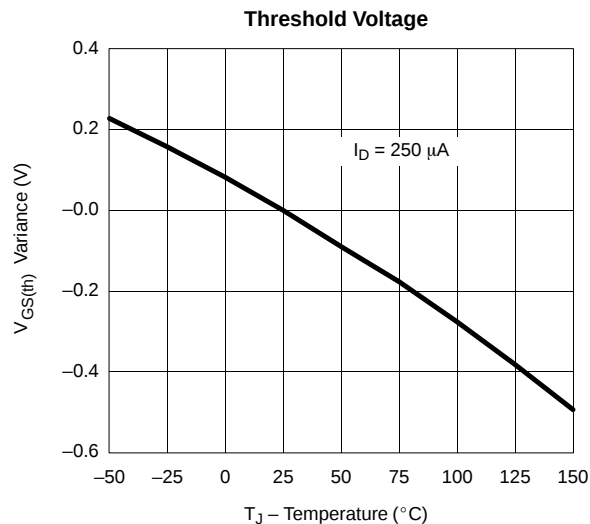
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	0.6			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}$, $V_{GS} = \pm 12\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16\ \text{V}$, $V_{GS} = 0\ \text{V}$			1	μA
		$V_{DS} = 16\ \text{V}$, $V_{GS} = 0\ \text{V}$, $T_J = 70^\circ\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\ \text{V}$, $V_{GS} = 4.5\ \text{V}$	30			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 4.5\ \text{V}$, $I_D = 5.2\ \text{A}$		0.022	0.026	Ω
		$V_{GS} = 2.5\ \text{V}$, $I_D = 4.4\ \text{A}$		0.029	0.036	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 10\ \text{V}$, $I_D = 5.2\ \text{A}$		23		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 0.9\ \text{A}$, $V_{GS} = 0\ \text{V}$		0.8	1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 10\ \text{V}$, $V_{GS} = 4.5\ \text{V}$, $I_D = 5.2\ \text{A}$		25	40	nC
Gate-Source Charge	Q_{gs}			3.7		
Gate-Drain Charge	Q_{gd}			8.1		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\ \text{V}$, $R_L = 10\ \Omega$ $I_D \cong 1\ \text{A}$, $V_{GEN} = 4.5\ \text{V}$, $R_G = 6\ \Omega$		25	50	ns
Rise Time	t_r			40	80	
Turn-Off Delay Time	$t_{d(off)}$			80	160	
Fall Time	t_f			45	90	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 0.9\ \text{A}$, $di/dt = 100\ \text{A}/\mu\text{s}$		40	80	

Notes

- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

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TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

SENSE DIE

